

Silicon PNP Power Transistors

BD744/A/B/C

DESCRIPTION

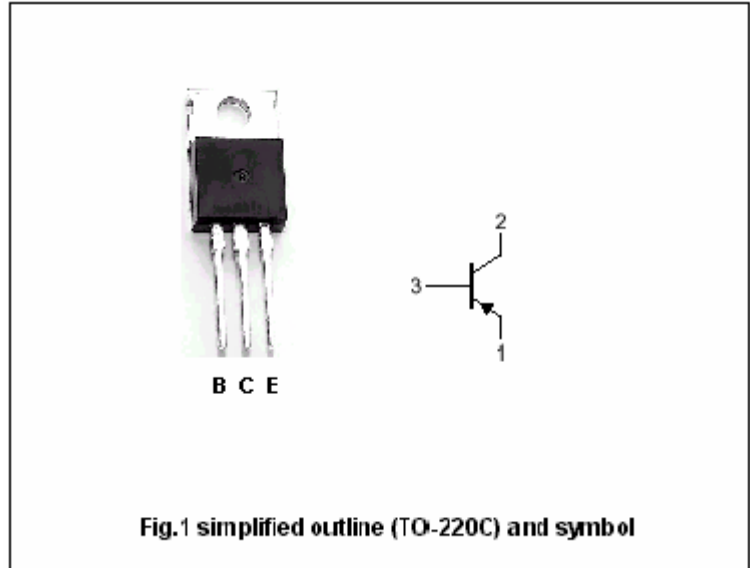
- With TO-220C package
- Complement to type BD743/A/B/C
- High current capability
- High power dissipation

APPLICATIONS

- For use in power linear and switching applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings (Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT	
V _{CBO}	Collector-base voltage	Open emitter	BD744	-50	V
			BD744A	-70	
			BD744B	-90	
			BD744C	-110	
V _{CEO}	Collector-emitter voltage	Open base	BD744	-45	V
			BD744A	-60	
			BD744B	-80	
			BD744C	-100	
V _{EBO}	Emitter-base voltage	Open collector	-5	V	
I _C	Collector current		-15	A	
I _{CM}	Collector current-peak		-20	A	
I _B	Base current		-5	A	
P _C	Collector power dissipation	T _C =25	90	W	
		T _a =25	2		
T _j	Junction temperature		150		
T _{stg}	Storage temperature		-65~150		

Silicon PNP Power Transistors

BD744/A/B/C

CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT	
V _{(BR)CEO}	Collector-emitter breakdown voltage	BD744	-45			V	
		BD744A	-60				
		BD744B	-80				
		BD744C	-100				
V _{CEsat-1}	Collector-emitter saturation voltage	I _C =-5 A; I _B =-0.5 A			-1.0	V	
V _{CEsat-2}	Collector-emitter saturation voltage	I _C =-15 A; I _B =-5 A			-3.0	V	
V _{BE-1}	Base-emitter on voltage	I _C =-5 A; V _{CE} =-4V			-1.0	V	
V _{BE-2}	Base-emitter on voltage	I _C =-15 A; V _{CE} =-4V			-3.0	V	
I _{CEO}	Collector cut-off current	BD744/A	V _{CE} =-30V; I _B =0			-0.1	mA
		BD744B/C	V _{CE} =-60V; I _B =0				
I _{CBO}	Collector cut-off current	BD744	V _{CE} =-50V; V _{BE} =0 T _C =125			-0.1 -5.0	mA
		BD744A	V _{CE} =-70V; V _{BE} =0 T _C =125			-0.1 -5.0	
		BD744B	V _{CE} =-90V; V _{BE} =0 T _C =125			-0.1 -5.0	
		BD744C	V _{CE} =-110V; V _{BE} =0 T _C =125			-0.1 -5.0	
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-0.5	mA	
h _{FE-1}	DC current gain	I _C =-1 A; V _{CE} =-4V	40				
h _{FE-2}	DC current gain	I _C =-5 A; V _{CE} =-4V	20		150		
h _{FE-3}	DC current gain	I _C =-15 A; V _{CE} =-4V	5				

Switching times resistive load

t _d	Delay time	I _C =-5 A; I _{B1} =-I _{B2} =-0.5 A V _{BE(off)} =4.2V; R _L =6 t _p =20 μs		0.02		μs
t _r	Rise time			0.12		μs
t _s	Storage time			0.6		μs
t _f	Fall time			0.3		μs

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal resistance junction to case	1.40	/W

Silicon PNP Power Transistors

BD744/A/B/C

PACKAGE OUTLINE

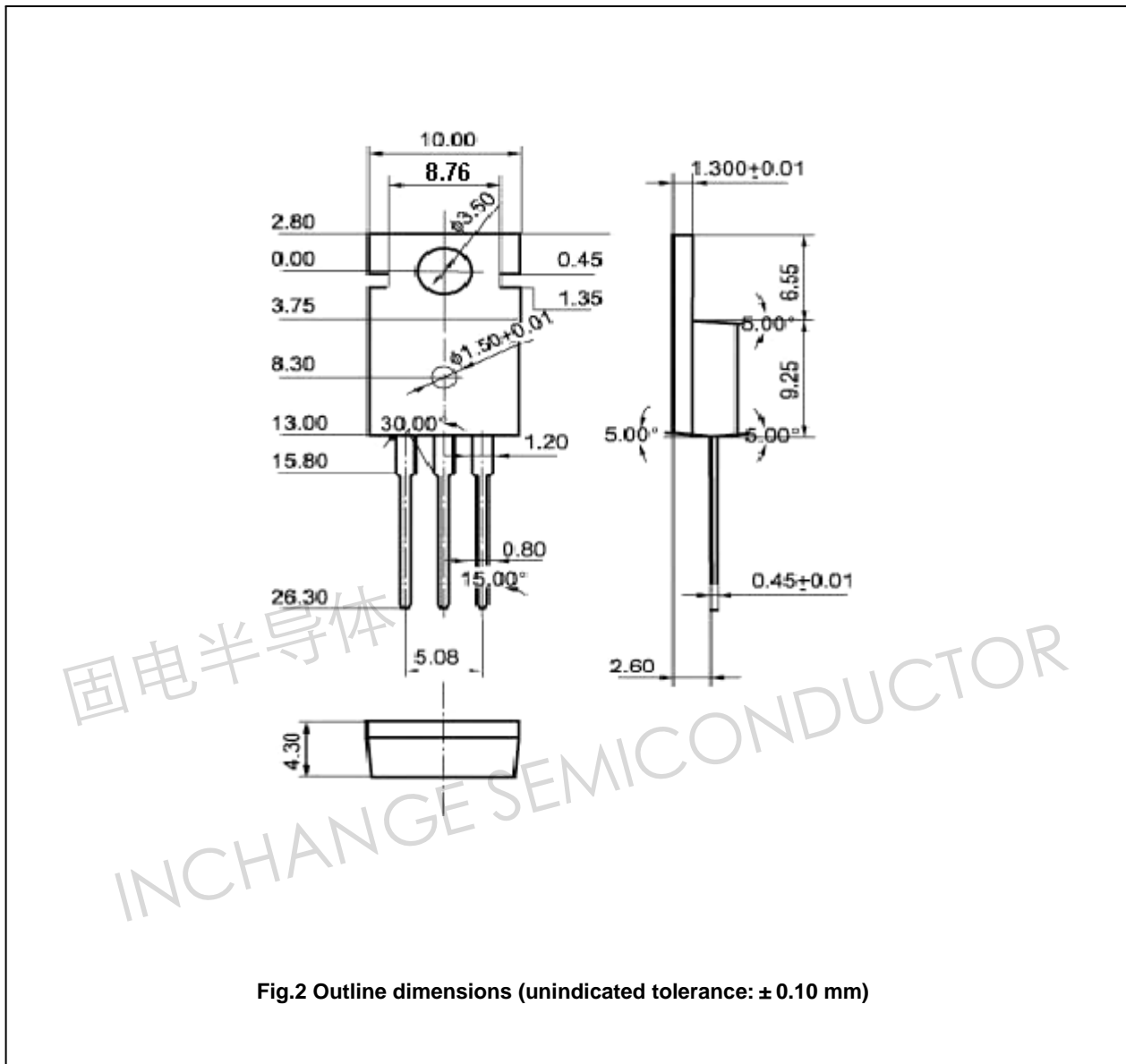


Fig.2 Outline dimensions (unindicated tolerance: ± 0.10 mm)